

TABLE OF CONTENTS

PREFACE	iii
CRYSTAL GROWTH AND WAFER PROCESSING	1
Application of Electric Current in Growing Silicon Single Crystals J.H. Wang	3
A Kinetic Model for P-type Doping in Silicon Epitaxy by CVD B. Mehta and M. Tao	12
Inhibiting Surface Roughness During the Thermal Desorption of Silicon A.F. Pun, X. Wang, J.B. Meeks and J.P. Zheng	23
The Saw-Damage-Induced Structural Defects on the Surface of Silicon Crystals J.M. Kim and Y.K. Kim	27
NITROGEN IN SILICON	37
Impurity Locking of Dislocations in Silicon * A. Giannattasio, J.D. Murphy, S. Senkader, R.J. Falster and P.R. Wilshaw	39
On the Influence of Nitrogen and Carbon on the Formation of Dislocations in Heavily Doped Silicon Wafers R. Winkler, R. Krautbauer and R. Pech	55
Improvement in the SIMS Measurement of Bulk Nitrogen in Silicon B.-S. Park, L. Wang and R. S. Hockett	60
Standardization of Nitrogen Analysis in CZ-Si by Charged Particle Activation Analysis K. Masumoto, T. Nozaki, H. Yagi, Y. Minai, Y. Saito, S. Futatsugawa and N. Inoue	69

*Invited paper

Formation and Control of Defects in Nitrogen Doped Silicon Crystals *	77
A. Huber, U. Lambert, W. Häckl and W.v. Ammon	
Nitrogen in Silicon: Properties and Impact on Grown-in Microdefects*	86
V.V. Voronkov and R. Falster	
Measurement of Nitrogen Concentration in CZ-Si below $10^{14}/\text{cm}^3$ by IR Absorption Spectroscopy	102
M. Nakatsu, A. Hashimoto, A. Natsume, N. Inoue and H. Ono	
Nitrogen in Thin Silicon Wafers Determined by Infrared Spectroscopy	109
V.D. Akhmetov, O. Lysytskiy and H. Richter	
FTIR Measurement of Nitrogen in Silicon Using Shuttle Type Sample Stage	121
M. Watanabe and N. Takenawa	
METALLIC CONTAMINATION AND GETTERING	133
Detection of Iron Contamination in Internally Gettered P-type Silicon Wafer by Lifetime Measurements	135
A. Haarahiltunen, H. Väinölä, M. Yki-Koski, E. Saarnilehto and J. Sinkkonen	
Pairing Reactions between Substitutional and Interstitial Defects Caused by the Same Transition Metal in Silicon Float Zone Crystals	146
H. Lemke and K. Irmscher	
Enhancement of Internal Gettering Efficiency of Iron by Low Temperature Nucleation	160
H. Väinölä, A. Haarahiltunen, E. Saarnilehto, M. Yli-Koski, J. Sinkkonen and O. Anttila	
Accurate Modeling of Copper Precipitation Kinetics Including Fermi Level Dependence	165
H.-W. Guo and S.T. Durham	

*Invited paper

Modeling of Internal Gettering for Metal Impurities by Oxide Precipitates in CZ-Si Wafers K. Sueoka	176
Thresholds for Effective Internal Gettering in Silicon Wafers R. Falster, V.V. Voronkov, V.Y. Resmik and M.G. Milvidskii	188
He-induced Nanocavities for the Gettering of Metallic Impurities in Silicon E. Ntsoenzok, R. Delamare, D. Alquier, C.L. Liu, S. Ashok and M.O. Ruault	202
Trapping Mechanisms by Cavities for Metallic Impurities in Monocrystalline Silicon G. Regula, R. El Bouayadi, B. Pichaud, M. Lancin and E. Ntsoenzok	208
Experimental Study and Simulation of Stress-Induced Cavities in Silicon K.V. Loiko, I.V. Peidous and W.R. Frensley	218
Defect Engineering and Control in Nanocrystalline Silicon D. Milovzorov	226
OXYGEN RELATED DEFECTS	235
Formation Mechanism of Voids and Oxide Precipitates in Silicon Crystals* A. Nakamura, T. Saishoji and T. Tomioka	237
Simplified Two-Dimensional Quantification of the Microdefect Distributions in Silicon Crystals Grown by Czochralski Process M.S. Kulkarni and V.V. Voronkov	254
Oxygen-Related Donors in Germanium doped Czochralski Silicon D. Yang, H. Li, X. Yu, X. Ma, D. Tian, L. Li and S. Que	268
Long-Time Relaxation of Silicon Resistivity after Annihilation of Thermal Donors G.I. Voronkova, A.V. Batunina, V.V. Voronkov, R. Falster and M. Porrini	275

*Invited paper

Oxygen Precipitation and Thermal Donor Formation in Pb and C-Doped n-type Czochralski Silicon	286
M.V. Neimash, M. Kras'ko, A. Kraitchinskii, V. Voytovych, O. Kabaldin, V. Tsmots, E. Simoen and C. Claeys	

IMPACT OF DEFECTS ON DEVICES	295
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Impact of Lanthanide Contamination on ULSI CMOS	297
W. Taylor, L. Lovejoy, P.J. Tobin, Z.X. Jiang, J. Lerma, J.-Y, Nguyen and R. Garcia	

Impact of STI Width and Spacing on the Stress Generation in Deep Submicron CMOS	307
A. Poyai, I. Rittaporn, E. Simoen, C. Claeys and R. Rooyackers	

Dielectric Degradation of Gate SiO ₂ Films by Cu Contamination Posterior to Polycrystalline Si Gate MOS Capacitor Fabrication	317
T. Onizawa, K. Higuchi, M. Goto, N. Tokuda, R. Hasunuma and K. Yamabe	

CHARACTERIZATION AND LIFETIME ANALYSIS	327
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Trace Metal Contamination Analysis of the Bevel and Edge Exclusion Area on Starting Silicon	329
C.M. Sparks and M.R. Beebe	

Effective Lifetime of Minority Carriers in Silicon: the Role of Heat- and Hydrogen Plasma Treatments	334
A. Ulyashin, E. Simoen, L. Carnel, S. De Wolf, H. Dekkers, J.M. Rafi, G. Beaucarne, J. Poortmans and C. Claeys	

Temperature Influence on the Generation Lifetime Determination Based on Drain Current Transients in Partially Depleted SOI nMOSFETs	346
J.A. Martino, J.M. Rafi, A. Mercha, E. Simoen and C. Claeys	

*Invited Paper

Single Spin Etching Behavior Analysis by Quality Engineering (Taguchi Method)	357
S. Itoh, M. Takano, Y. Kozuki, M. Watanabe, R. Matsumoto and H. Kruwinus	
PLASMA AND RADIATION-INDUCED DEFECTS	
Irradiation-induced Deep Levels in Silicon*	369
R. Siemieniec, F.-J. Niedermostheide, H.-J. Schulze, W. Sudkamp, U. Kellner-Werdehausen and J. Lutz	
Thermal Evolution of Hydrogen Related Defects in Silicon Investigated by μ-Raman Spectroscopy	385
Y. Ma, Y.L. Huang, R. Job, W.R. Fahrner, M.-F. Beaufort and J.-F. Barbot	
Radiation-Induced Deep Levels in Lead- and Tin-Doped n-Type Czochralski Silicon	395
M.-L. David, E. Simoen, C. Claeys, V. Neimash, M. Kras'ko, A. Kraitchinski, V. Voytovuch, V. Tishcenko and J.F. Barbot	
Morphology and Stress Investigations of Surface and Subsurface Regions of Plasma Hydrogenated and Annealed Czochralski Silicon	407
R. Job, Y. Ma, Y.L. Huang and W. Dungen	
Hydrogen Diffusion Characterized by Hydrogen Enhanced Thermal Donor Formation in p-Type Czochralski Silicon at Temperatures Between 350 and 450°C	419
Y.L. Huang, Y. Ma, R. Job and W.R. Fahrner	
Authors Index	429
Subject Index	433

*Invited paper